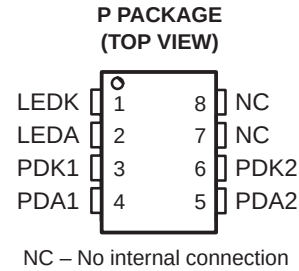


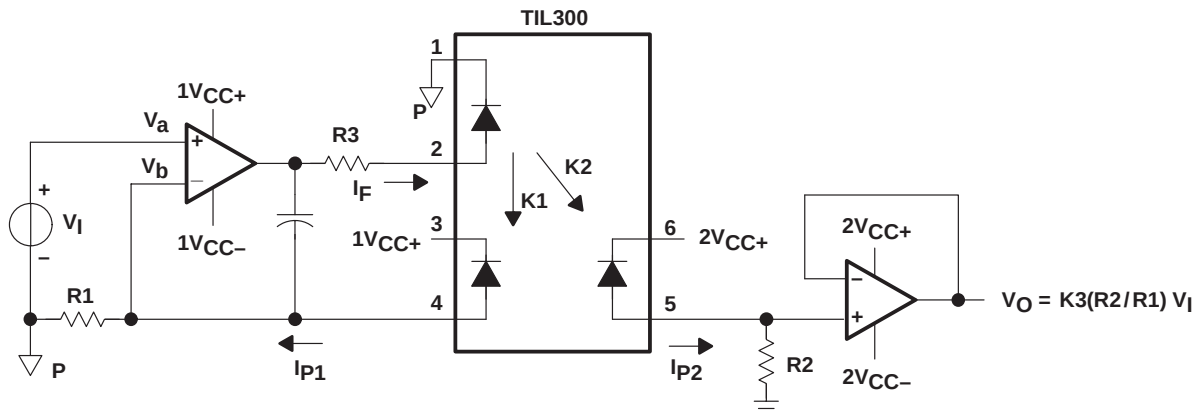
- ac or dc Signal Coupling
- Wide Bandwidth . . . >200 kHz
- High Transfer-Gain Stability . . . $\pm 0.05\%/^{\circ}\text{C}$
- 3500 V Peak Isolation
- UL Approval Pending
- Applications
 - Power-Supply Feedback
 - Medical-Sensor Isolation
 - Opto Direct-Access Arrangement (DAA)
 - Isolated Process-Control Transducers



description

The TIL300 precision linear optocoupler consists of an infrared LED irradiating an isolated feedback photodiode and an output photodiode in a bifurcated arrangement. The feedback photodiode captures a percentage of the flux of the LED and generates a control signal that can be used to regulate the LED drive current. This technique is used to compensate for the nonlinear time and temperature characteristics of the LED. The output-side photodiode produces an output signal that is linearly proportional to the servo-optical flux emitted from the LED.

A typical application circuit (shown in Figure 1) uses an operational amplifier as the input to drive the LED. The feedback photodiode sources current through R1, which is connected to the inverting input of the input operational amplifier. The photocurrent I_{P1} assumes a magnitude that satisfies the relationship $I_{P1} = V_i/R1$. The magnitude of the current is directly proportional to the LED current through the feedback transfer gain K1 ($V_i/R1 = K1 \times I_F$). The operational amplifier supplies LED current to produce sufficient photocurrent to keep the node voltage V_b equal to node voltage V_a .



- NOTES: A. K1 is servo current gain, the ratio of the feedback photodiode current (I_{P1}) to the input LED current (I_F), i.e. $K1 = I_{P1}/I_F$.
 B. K2 is forward gain, the ratio of the output photodiode current (I_{P2}) to the input LED current (I_F), i.e. $K2 = I_{P2}/I_F$.
 C. K3 is transfer gain, the ratio of the forward gain to the servo gain, i.e. $K3 = K2/K1$.

Figure 1. Typical Application Circuit



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS
INSTRUMENTS**

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TIL300, TIL300A

PRECISION LINEAR OPTOCOUPLER

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Terminal Functions

TERMINAL NAME	NO.	I/O	DESCRIPTION
LEDK	1		LED cathode
LEDA	2		LED anode
PDK1	3		Photodiode 1 cathode
PDA1	4		Photodiode 1 anode
PDA2	5		Photodiode 2 anode
PDK2	6		Photodiode 2 cathode
NC	7		No internal connection
NC	8		No internal connection

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Emitter

Continuous total power dissipation (see Note 1) 160 mW
 Input LED forward current, I_F 60 mA
 Surge current with pulse width < 10 μ s 250 mA
 Reverse voltage, V_R 5 V
 Reverse current, I_R 10 μ A

Detector

Continuous power dissipation (see Note 2) 50 mW
 Reverse voltage, V_R 50 V

Coupler

Continuous total power dissipation (see Note 3) 210 mW
 Storage temperature, T_{stg} -55°C to 150°C
 Operating temperature, T_A -55°C to 100°C
 Input-to-output voltage 3535 V_{peak}
 Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds 260°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Derate linearly from 25°C at a rate of 2.66 mW/°C.
 2. Derate linearly from 25°C at a rate of 0.66 mW/°C.
 3. Derate linearly from 25°C at a rate of 3.33 mW/°C.



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electrical characteristics at $T_A = 25^\circ\text{C}$

Emitter

PARAMETER		CONDITIONS	MIN	TYP [†]	MAX	UNIT
V_F	Forward voltage	$I_F = 10\text{ mA}$		1.25	1.50	V
	Temperature coefficient of V_F			-2.2		mV/ $^\circ\text{C}$
I_R	Reverse current	$V_R = 5\text{ V}$			10	μA
t_r	Rise time	$I_F = 10\text{ mA}$, $\Delta I_F = 2\text{ mA}$		1		μs
t_f	Fall time	$I_F = 10\text{ mA}$, $\Delta I_F = 2\text{ mA}$		1		μs
C_j	Junction capacitance	$V_F = 0$, $f = 1\text{ MHz}$		15		pF

Detector

PARAMETER		CONDITIONS	MIN	TYP [†]	MAX	UNIT
$I_{DK}^\dagger$	Dark current	$V_R = 15\text{ V}$, $I_F = 0$			25	nA
	Open circuit voltage	$I_F = 10\text{ mA}$		0.5		V
I_{OS}	Short circuit current limit	$I_F = 10\text{ mA}$		80		μA
C_j	Junction capacitance	$V_F = 0$, $f = 1\text{ MHz}$		12		pF

Coupler

PARAMETER		CONDITIONS	MIN	TYP [†]	MAX	UNIT
$K1^\ddagger$	Servo current gain	$I_F = 1\text{ mA}$	0.3%	0.7%	1.5%	
		$I_F = 10\text{ mA}$	0.5%	1.25%	2%	
$K2^\S$	Forward current gain	$I_F = 1\text{ mA}$	0.3%	0.7%	1.5%	
		$I_F = 10\text{ mA}$	0.5%	1.25%	2%	
$K3^\P$	Transfer gain	Detector bias voltage = -15 V	$I_F = 1\text{ mA}$	0.75	1	1.25
			$I_F = 10\text{ mA}$	0.75	1	1.25
			$I_F = 1\text{ mA}$	0.9	1	1.10
			$I_F = 10\text{ mA}$	0.9	1	1.10
	Gain temperature coefficient	$I_F = 10\text{ mA}$	K1/K2		-0.5	%/ $^\circ\text{C}$
			K3		± 0.005	
$\Delta K3^\#$	Transfer gain linearity	$I_F = 1\text{ to }10\text{ mA}$			$\pm 0.25\%$	
		$I_F = 1\text{ to }10\text{ mA}$, $T_A = 0\text{ to }75^\circ\text{C}$			$\pm 0.5\%$	
BW	Bandwidth	$I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, $I_{F(\text{MODULATION})} = \pm 2\text{ mA}$			200	kHz
t_r	Rise time	$I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, $I_{F(\text{MODULATION})} = \pm 2\text{ mA}$			1.75	μs
t_f	Fall time	$I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, $I_{F(\text{MODULATION})} = \pm 2\text{ mA}$			1.75	μs
$V_{iso}^\dagger$	Peak Isolation voltage	$I_{IO} = 10\text{ }\mu\text{A}$, $f = 60\text{ Hz}$, time = 1 minute			3535	V

[†] This symbol is not currently listed within EIA or JEDEC standards for semiconductor symbology.

[‡] Servo current gain ($K1$) is the ratio of the feedback photodiode current (I_{P1}) to the input LED current (I_F), i.e. $K1 = I_{P1}/I_F$.

[§] Forward gain ($K2$) is the ratio of the output photodiode current (I_{P2}) to the input LED current (I_F), i.e. $K2 = I_{P2}/I_F$.

[¶] Transfer gain ($K3$) is the ratio of the forward gain to the servo gain, i.e. $K3 = K2/K1$.

[#] Transfer gain linearity ($\Delta K3$) is the percent deviation of the transfer gain $K3$ as a function of LED input current (I_F) or the package temperature.

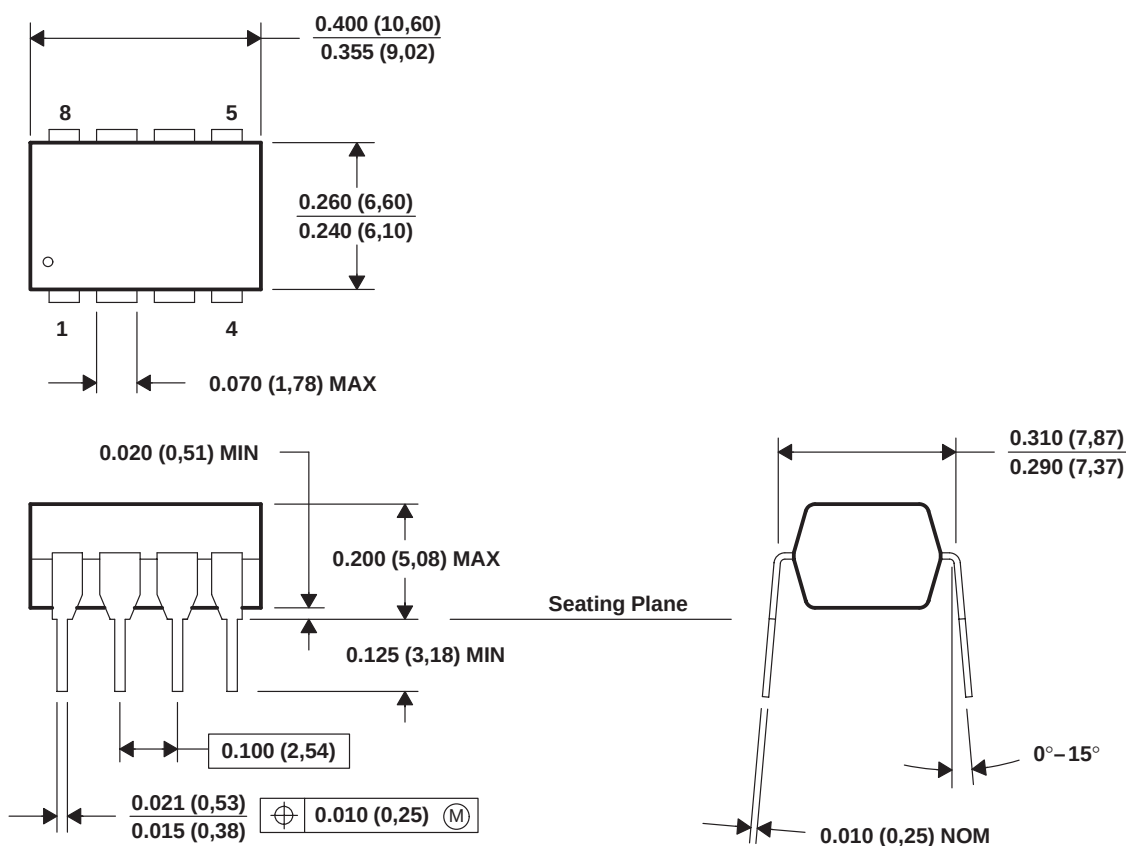
PRECISION LINEAR OPTOCOUPLER

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MECHANICAL DATA

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



4040082 / B 03/95

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS-001

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